

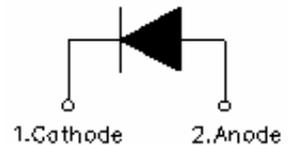
MBR1045 SCHOTTKY RECTIFIER

Applications:

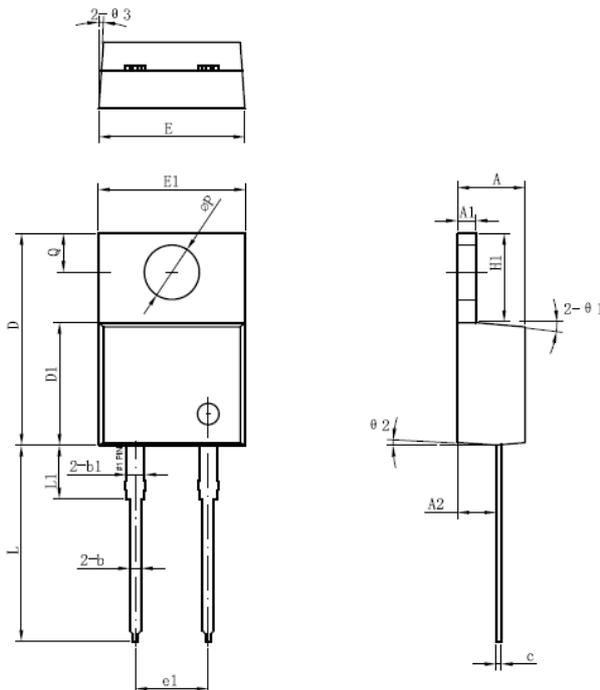
- Switching power supply
- Converters
- Free-Wheeling diodes
- Reverse battery protection
- Center tap configuration

Features:

- 150 °C T_J operation
- Low forward voltage drop
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- This is a Pb – Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

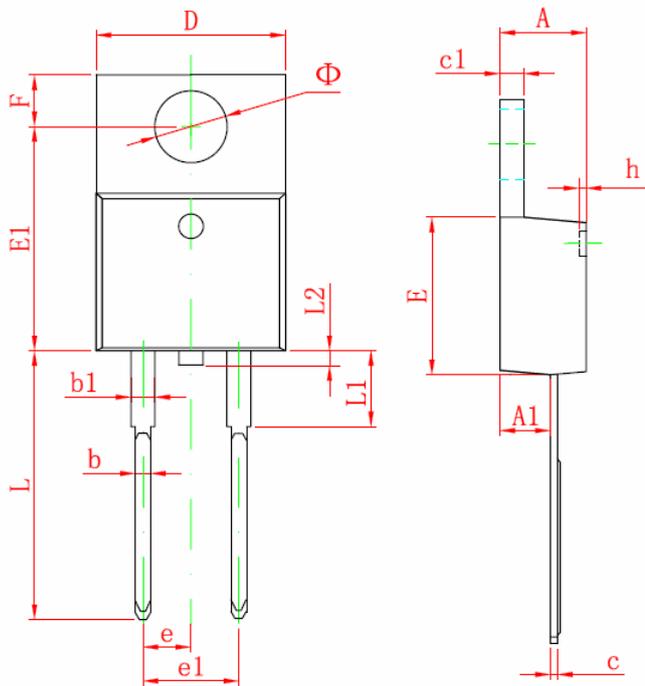


Mechanical Dimensions (In mm)



OPTION 1(HD)

Symbol	Dimensions in millimeters		
	Min.	Typical	Max.
A	4.55	4.70	4.85
A1	1.17	1.27	1.37
A2	2.59	2.69	2.89
b	0.71	0.81	0.96
b1		1.27	
c	0.36	0.38	0.61
D	14.64	14.94	15.24
D1	8.55	8.07	8.85
E	10.01	10.16	10.31
E1	9.98	10.18	10.38
e1		5.08	
H1	6.04	6.24	6.44
L	13.00	13.86	14.08
L1		3.80	
ΦP	3.74	3.84	4.04
Q	2.54	2.74	2.94
Θ1		5°	
Θ2		4°	
Θ3		4°	



Symbol	Dimensions in Millimeters	
	Min	Max
A	4.470	4.670
A1	2.520	2.820
b	0.710	0.910
b1	1.170	1.370
c	0.310	0.530
c1	1.170	1.370
D	10.010	10.310
E	8.500	8.900
E1	12.060	12.460
e	2.540 TYP	
e1	4.980	5.180
F	2.590	2.890
h	0.000	0.300
L	13.400	13.800
L1	3.560	3.960
L2		1.000
Φ	3.735	3.935

OPTION 2(CJ)

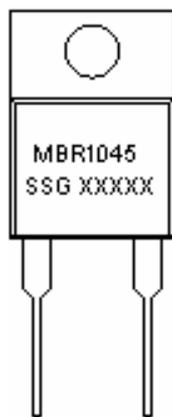
TO-220AC



Technical Data
Data Sheet N0615, Rev. -

Green Products

Marking Diagram:



Where XXXXX is YYWWL

MBR = Device Type
10 = Forward Current (10A)
45 = Reverse Voltage (45V)
SSG = SSG
YY = Year
WW = Week
L = Lot Number

Cautions: Molding resin
Epoxy resin UL:94V-0

Ordering Information:

Device	Package	Shipping
MBR1045	TO-220AC(Pb-Free)	50pcs/ tube

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification.

Maximum Ratings:

Characteristics	Symbol	Condition	Max.	Units
Peak Inverse Voltage	V_{RWM}	-	45	V
Max. Average Forward Current	$I_{F(AV)}$	50% duty cycle @ $T_C=115^\circ\text{C}$, rectangular wave form	10	A
Max. Peak One Cycle Non-Repetitive Surge Current	I_{FSM}	8.3 ms, half Sine pulse	150	A



Electrical Characteristics:

Characteristics	Symbol	Condition	Max.	Units
Max. Forward Voltage Drop	V_{F1}	@ 10 A, Pulse, $T_J = 25\text{ }^\circ\text{C}$	0.65	V
Max. Reverse Current	I_{R1}	@ $V_R = \text{rated } V_R$ $T_C = 25\text{ }^\circ\text{C}$	1.0	mA
	I_{R2}	@ $V_R = \text{rated } V_R$ $T_C = 125\text{ }^\circ\text{C}$	15	mA
Max. Junction Capacitance	C_T	@ $V_R = 5\text{V}$, $T_C = 25\text{ }^\circ\text{C}$ $f_{SIG} = 1\text{MHz}$	400	pF
Max. Voltage Rate of Change	dv/dt	-	10,000	V/ μs

* Pulse Width < 300 μs , Duty Cycle <2%

Thermal-Mechanical Specifications:

Characteristics	Symbol	Condition	Specification	Units
Max. Junction Temperature	T_J	-	-55 to +150	$^\circ\text{C}$
Max. Storage Temperature	T_{stg}	-	-55 to +150	$^\circ\text{C}$
Maximum Thermal Resistance Junction to Case	$R_{\theta JC}$	DC operation	2.0	$^\circ\text{C/W}$
Approximate Weight	wt	-	1.85	g
Case Style	TO-220AC			

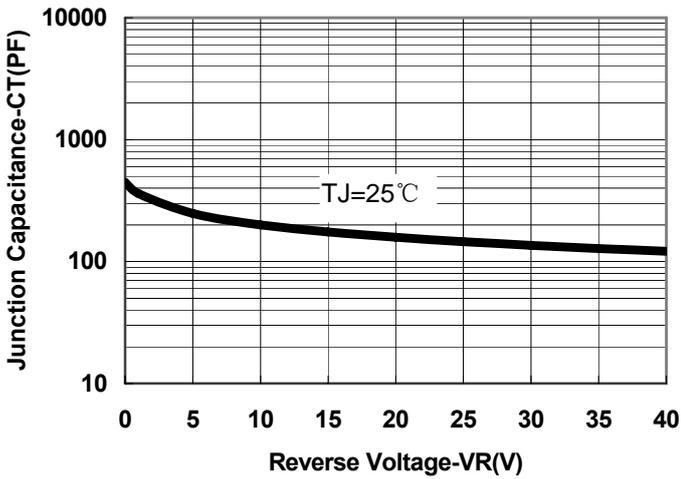


Fig.1-Typical Junction Capacitance

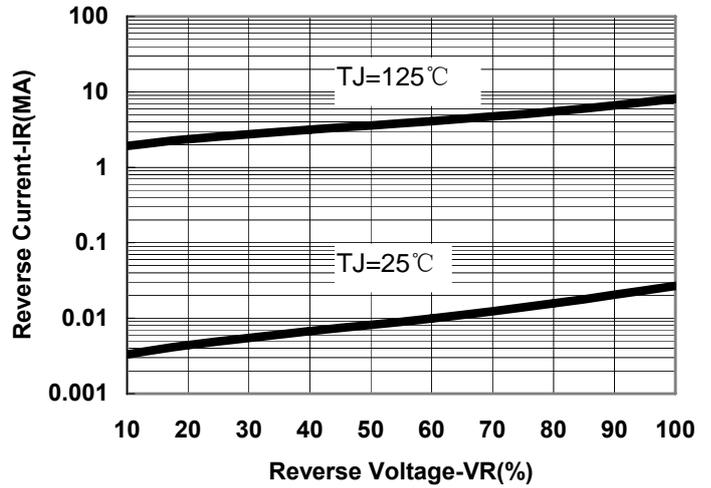


Fig.2-Typical Reverse Characteristics

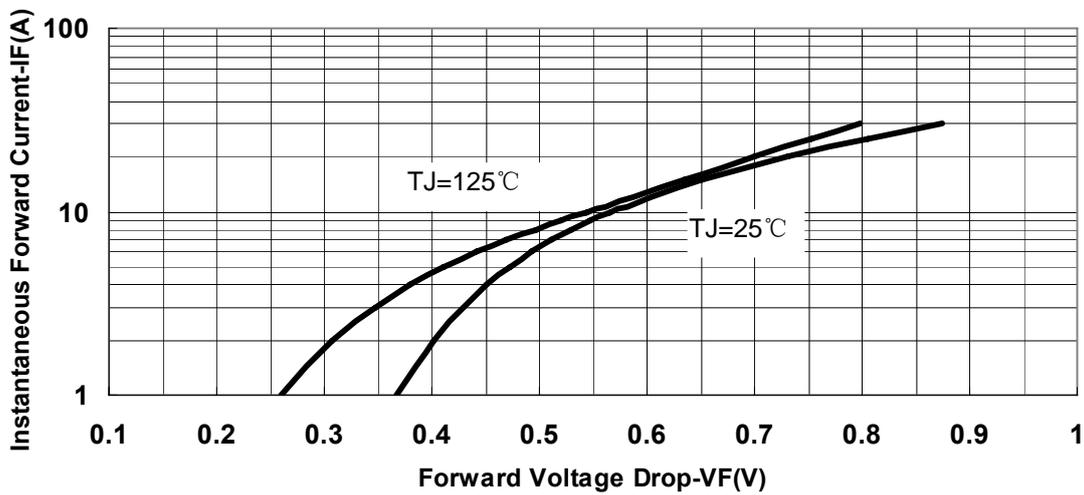


Fig.3-Typical Instantaneous Forward Voltage Characteristics

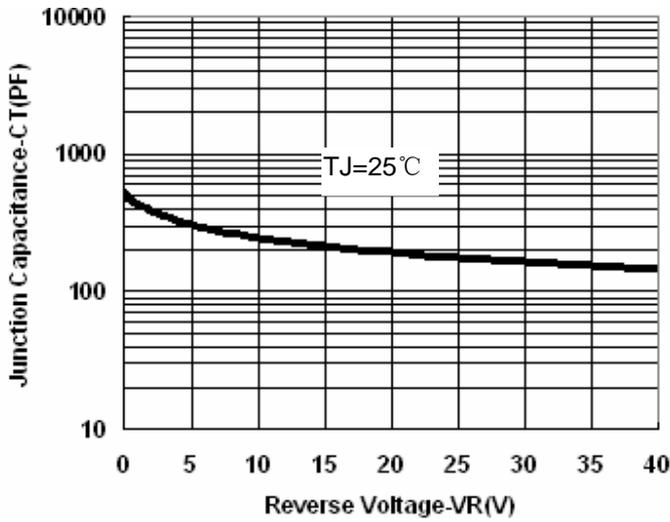


Fig.1-Typical Junction Capacitance

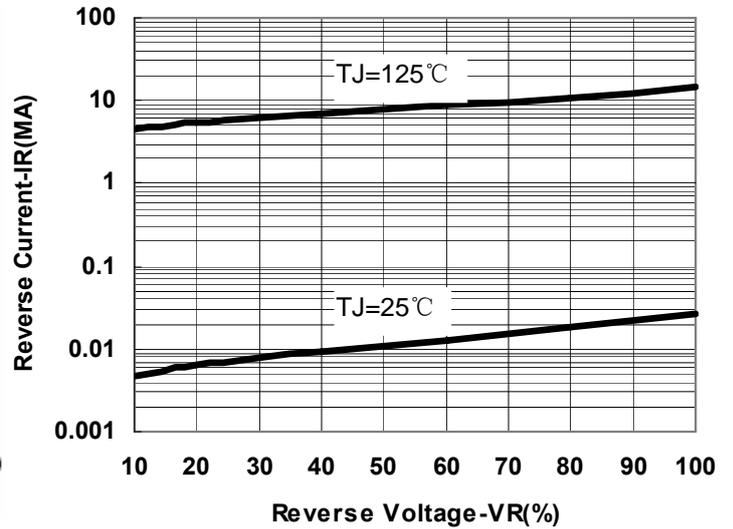


Fig.2-Typical Reverse Characteristics

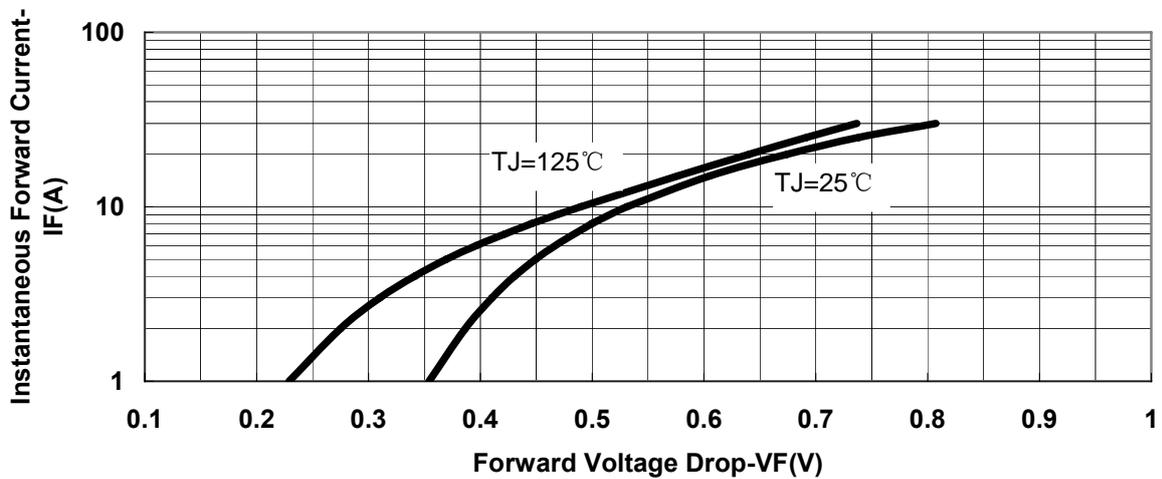


Fig.3-Typical Instantaneous Forward Voltage Characteristics



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